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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	STM8
Core Size	8-Bit
Speed	16MHz
Connectivity	I²C, IrDA, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, IR, POR, PWM, WDT
Number of I/O	41
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 25x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	48-UFQFN Exposed Pad
Supplier Device Package	48-UFQFPN (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm8l151c8u3

2.1 Device overview

Table 2. Medium-density STM8L151x4/6 and STM8L152x4/6 low-power device features and peripheral counts

Features		STM8L151Gx		STM8L15xKx		STM8L15xCx	
Flash (Kbyte)		16	32	16	32	16	32
Data EEPROM (Kbyte)		1					
RAM (Kbyte)		2					
LCD		No		4x17 (1)		4x28 (1)	
Timers	Basic	1 (8-bit)					
	General purpose	2 (16-bit)					
	Advanced control	1 (16-bit)					
Communication interfaces	SPI	1					
	I2C	1					
	USART	1					
GPIOs		26(3)		30 (2)(3) or 29 (1)(3)		41(3)	
12-bit synchronized ADC (number of channels)		1 (18)		1 (22 (2) or 21 (1))		1 (25)	
12-Bit DAC (number of channels)		1 (1)					
Comparators COMP1/COMP2		2					
Others		RTC, window watchdog, independent watchdog, 16-MHz and 38-kHz internal RC, 1- to 16-MHz and 32-kHz external oscillator					
CPU frequency		16 MHz					
Operating voltage		1.8 V to 3.6 V (down to 1.65 V at power down)					
Operating temperature		-40 to +85 °C/ -40 to +105 °C / -40 to +125 °C					
Packages		UFQFPN28 (4x4; 0.6 mm thickness) WLCSP28		LQFP32(7x7) UFQFPN32 (5x5; 0.6 mm thickness)		LQFP48 UFQFPN48 (4x4; 0.6 mm thickness)	

1. STM8L152xx versions only
2. STM8L151xx versions only
3. The number of GPIOs given in this table includes the NRST/PA1 pin but the application can use the NRST/PA1 pin as general purpose output only (PA1).

Table 5. Medium-density STM8L151x4/6, STM8L152x4/6 pin description (continued)

Pin number				Pin name	Type	I/O level	Input			Output			Main function (after reset)	Default alternate function
LQFP48/UFQFPN48	LQFP32/UFQFPN32	UFQFPN28	WLCSP28				floating	wpu	Ext. interrupt	High sink/source	OD	PP		
30	-	-	-	PB6/[*SPI1_MOSI*](4)/ LCD_SEG16(2)/ ADC1_IN12/COMP1_INP	I/O	TT (3)	**X**	X	X	HS	X	X	**Port B6**	*[SPI1 master out/slave in]*/ LCD segment 16 / ADC1_IN12 / Comparator 1 positive input
-	19	18	F1	PB6/*[SPI1_MOSI]*(4)/ LCD_SEG16(2)/ ADC1_IN12/COMP1_INP/ DAC_OUT	I/O	TT (3)	**X**	X	X	HS	X	X	**Port B6**	*[SPI1 master out]*/ slave in / LCD segment 16 / ADC1_IN12 / DAC output / Comparator 1 positive input
31	20	19	E1	PB7/*[SPI1_MISO]*(4)/ LCD_SEG17(2)/ ADC1_IN11/COMP1_INP	I/O	TT (3)	**X**	X	X	HS	X	X	**Port B7**	*[SPI1 master in- slave out]* / LCD segment 17 / ADC1_IN11 / Comparator 1 positive input
37	25	21	B1	PC0(5)/I2C1_SDA	I/O	FT	**X**		X		T(7)		**Port C0**	I2C1 data
38	26	22	A1	PC1(5)/I2C1_SCL	I/O	FT	**X**		X		T(7)		**Port C1**	I2C1 clock
41	27	23	B2	PC2/USART1_RX/ LCD_SEG22/ADC1_IN6/ COMP1_INP/VREFINT	I/O	TT (3)	**X**	X	X	HS	X	X	**Port C2**	USART1 receive / LCD segment 22 / ADC1_IN6 / Comparator 1 positive input / Internal voltage reference output
42	28	24	A2	PC3/USART1_TX/ LCD_SEG23(2)/ ADC1_IN5/COMP1_INP/ COMP2_INM	I/O	TT (3)	**X**	X	X	HS	X	X	**Port C3**	USART1 transmit / LCD segment 23 / ADC1_IN5 / Comparator 1 positive input / Comparator 2 negative input
43	29	25	C2	PC4/USART1_CK/ I2C1_SMB/CCO/ LCD_SEG24(2)/ ADC1_IN4/COMP2_INM/ COMP1_INP	I/O	TT (3)	**X**	X	X	HS	X	X	**Port C4**	USART1 synchronous clock / I2C1_SMB / Configurable clock output / LCD segment 24 / ADC1_IN4 / Comparator 2 negative input / Comparator 1 positive input

Table 5. Medium-density STM8L151x4/6, STM8L152x4/6 pin description (continued)

Pin number				Pin name	Type	I/O level	Input			Output			Main function (after reset)	Default alternate function
LQFP48/UFQFPN48	LQFP32/UFQFPN32	UFQFPN28	WLCSP28				floating	wpu	Ext. interrupt	High sink/source	OD	PP		
-	8	7	G4	$V_{DD1}/V_{DDA}/V_{REF+}$	S	-	-	-	-	-	-	-	Digital power supply / Analog supply voltage / ADC1 positive voltage reference	
9	7	6	F4	$V_{SS1}/V_{SSA}/V_{REF-}$	S	-	-	-	-	-	-	-	I/O ground / Analog ground voltage / ADC1 negative voltage reference	
39	-	-	-	V_{DD2}	S	-	-	-	-	-	-	-	IOs supply voltage	
40	-	-	-	V_{SS2}	S	-	-	-	-	-	-	-	IOs ground voltage	
1	32	28	A4	PA0(9)/*[USART1_CK]*(4)/ SWIM/BEEP/IR_TIM (10)	I/O		X	**X**(9)	X	HS (10)	X	X	**Port A0**	*[USART1 synchronous clock]*(4) / SWIM input and output / Beep output / Infrared Timer output

1. At power-up, the PA1/NRST pin is a reset input pin with pull-up. To be used as a general purpose pin (PA1), it can be configured only as output open-drain or push-pull, not as a general purpose input. Refer to Section *Configuring NRST/PA1 pin as general purpose output* in the STM8L15x and STM8L16x reference manual (RM0031).
2. Available on STM8L152xx devices only.
3. In the 3.6 V tolerant I/Os, protection diode to V_{DD} is not implemented.
4. [ ] Alternate function remapping option (if the same alternate function is shown twice, it indicates an exclusive choice not a duplication of the function).
5. In the 5 V tolerant I/Os, protection diode to V_{DD} is not implemented.
6. A pull-up is applied to PB0 and PB4 during the reset phase. These two pins are input floating after reset release.
7. In the open-drain output column, 'T' defines a true open-drain I/O (P-buffer, weak pull-up and protection diode to V_{DD} are not implemented).
8. Available on STM8L151xx devices only.
9. The PA0 pin is in input pull-up during the reset phase and after reset release.
10. High Sink LED driver capability available on PA0.

Note: The slope control of all GPIO pins, except true open drain pins, can be programmed. By default, the slope control is limited to 2 MHz.

Table 9. General hardware register map (continued)

Address	Block	Register label	Register name	Reset status
0x00 5230	USART1	USART1_SR	USART1 status register	0xC0
0x00 5231		USART1_DR	USART1 data register	undefined
0x00 5232		USART1_BRR1	USART1 baud rate register 1	0x00
0x00 5233		USART1_BRR2	USART1 baud rate register 2	0x00
0x00 5234		USART1_CR1	USART1 control register 1	0x00
0x00 5235		USART1_CR2	USART1 control register 2	0x00
0x00 5236		USART1_CR3	USART1 control register 3	0x00
0x00 5237		USART1_CR4	USART1 control register 4	0x00
0x00 5238		USART1_CR5	USART1 control register 5	0x00
0x00 5239		USART1_GTR	USART1 guard time register	0x00
0x00 523A		USART1_PSCR	USART1 prescaler register	0x00
0x00 523B to 0x00 524F	Reserved area (21 bytes)			

9.3.2 Embedded reset and power control block characteristics

Table 19. Embedded reset and power control block characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_{VDD}	V_{DD} rise time rate	BOR detector enabled	0(1)	-	∞(1)	µs/V
	V_{DD} fall time rate	BOR detector enabled	20(1)	-	∞(1)	
t_{TEMP}	Reset release delay	V_{DD} rising BOR detector enabled	-	3	-	ms
		V_{DD} rising BOR detector disabled	-	1	-	
V_{PDR}	Power-down reset threshold	Falling edge	1.30(2)	1.50	1.65	V
V_{BOR0}	Brown-out reset threshold 0 (BOR_TH[2:0]=000)	Falling edge	1.67	1.70	1.74	V
		Rising edge	1.69	1.75	1.80	
V_{BOR1}	Brown-out reset threshold 1 (BOR_TH[2:0]=001)	Falling edge	1.87	1.93	1.97	
		Rising edge	1.96	2.04	2.07	
V_{BOR2}	Brown-out reset threshold 2 (BOR_TH[2:0]=010)	Falling edge	2.22	2.3	2.35	
		Rising edge	2.31	2.41	2.44	
V_{BOR3}	Brown-out reset threshold 3 (BOR_TH[2:0]=011)	Falling edge	2.45	2.55	2.60	
		Rising edge	2.54	2.66	2.7	
V_{BOR4}	Brown-out reset threshold 4 (BOR_TH[2:0]=100)	Falling edge	2.68	2.80	2.85	
		Rising edge	2.78	2.90	2.95	
V_{PVD0}	PVD threshold 0	Falling edge	1.80	1.84	1.88	V
		Rising edge	1.88	1.94	1.99	
V_{PVD1}	PVD threshold 1	Falling edge	1.98	2.04	2.09	
		Rising edge	2.08	2.14	2.18	
V_{PVD2}	PVD threshold 2	Falling edge	2.2	2.24	2.28	
		Rising edge	2.28	2.34	2.38	
V_{PVD3}	PVD threshold 3	Falling edge	2.39	2.44	2.48	
		Rising edge	2.47	2.54	2.58	
V_{PVD4}	PVD threshold 4	Falling edge	2.57	2.64	2.69	
		Rising edge	2.68	2.74	2.79	
V_{PVD5}	PVD threshold 5	Falling edge	2.77	2.83	2.88	
		Rising edge	2.87	2.94	2.99	
V_{PVD6}	PVD threshold 6	Falling edge	2.97	3.05	3.09	
		Rising edge	3.08	3.15	3.20	

In the following table, data is based on characterization results, unless otherwise specified.

Table 24. Total current consumption and timing in Active-halt mode at V_{DD} = 1.65 V to 3.6 V

Symbol	Parameter	Conditions (1)			Typ	Max	Unit
$I_{DD(AH)}$	Supply current in Active-halt mode	LSI RC (at 38 kHz)	LCD OFF(2)	T_A = -40 °C to 25 °C	0.9	2.1	µA
				T_A = 55 °C	1.2	3	
				T_A = 85 °C	1.5	3.4	
				T_A = 105 °C	2.6	6.6	
				T_A = 125 °C	5.1	12	
			LCD ON (static duty/ external V_{LCD}) (3)	T_A = -40 °C to 25 °C	1.4	3.1	
				T_A = 55 °C	1.5	3.3	
				T_A = 85 °C	1.9	4.3	
				T_A = 105 °C	2.9	6.8	
				T_A = 125 °C	5.5	13	
			LCD ON (1/4 duty/ external V_{LCD}) (4)	T_A = -40 °C to 25 °C	1.9	4.3	
				T_A = 55 °C	1.95	4.4	
				T_A = 85 °C	2.4	5.4	
				T_A = 105 °C	3.4	7.6	
				T_A = 125 °C	6.0	15	
			LCD ON (1/4 duty/ internal V_{LCD}) (5)	T_A = -40 °C to 25 °C	3.9	8.75	
				T_A = 55 °C	4.15	9.3	
				T_A = 85 °C	4.5	10.2	
				T_A = 105 °C	5.6	13.5	
				T_A = 125 °C	6.8	16.3	

Table 28. Current consumption under external reset

Symbol	Parameter	Conditions		Typ	Unit
$I_{DD(RST)}$	Supply current under external reset (1)	All pins are externally tied to V_{DD}	V_{DD} = 1.8 V	48	µA
			V_{DD} = 3 V	76	
			V_{DD} = 3.6 V	91	

1. All pins except PA0, PB0 and PB4 are floating under reset. PA0, PB0 and PB4 are configured with pull-up under reset.

9.3.4 Clock and timing characteristics

HSE external clock (HSEBYP = 1 in CLK_ECKCR)

Subject to general operating conditions for V_{DD} and T_A.

Table 29. HSE external clock characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSE_ext}	External clock source frequency(1)	-	1	-	16	MHz
V_{HSEH}	OSC_IN input pin high level voltage		0.7 x V_{DD}	-	V_{DD}	V
V_{HSEL}	OSC_IN input pin low level voltage		V_{SS}	-	0.3 x V_{DD}	
$C_{in(HSE)}$	OSC_IN input capacitance(1)	-	-	2.6	-	pF
I_{LEAK_HSE}	OSC_IN input leakage current	$V_{SS} < V_{IN} < V_{DD}$	-	-	±1	µA

1. Data guaranteed by design.

LSE external clock (LSEBYP=1 in CLK_ECKCR)

Subject to general operating conditions for V_{DD} and T_A.

Table 30. LSE external clock characteristics

Symbol	Parameter	Min	Typ	Max	Unit
f_{LSE_ext}	External clock source frequency(1)	-	32.768	-	kHz
V_{LSEH}(2)	OSC32_IN input pin high level voltage	0.7 x V_{DD}	-	V_{DD}	V
V_{LSEL}(2)	OSC32_IN input pin low level voltage	V_{SS}	-	0.3 x V_{DD}	
$C_{in(LSE)}$	OSC32_IN input capacitance(1)	-	0.6	-	pF
I_{LEAK_LSE}	OSC32_IN input leakage current	-	-	±1	µA

1. Data guaranteed by design.
2. Data based on characterization results.

Table 38. I/O static characteristics

Symbol	Parameter	Conditions(1)	Min	Typ	Max	Unit
V_{IL}	Input low level voltage(2)	Input voltage on true open-drain pins (PC0 and PC1)	V_{SS}-0.3	-	0.3 x V_{DD}	V
		Input voltage on five-volt tolerant (FT) pins (PA7 and PE0)	V_{SS}-0.3	-	0.3 x V_{DD}	
		Input voltage on 3.6 V tolerant (TT) pins	V_{SS}-0.3	-	0.3 x V_{DD}	
		Input voltage on any other pin	V_{SS}-0.3	-	0.3 x V_{DD}	
V_{IH}	Input high level voltage (2)	Input voltage on true open-drain pins (PC0 and PC1) with V_{DD} < 2 V	0.70 x V_{DD}	-	5.2	V
		Input voltage on true open-drain pins (PC0 and PC1) with $V_{DD} \geq 2$ V		-	5.5	
		Input voltage on five-volt tolerant (FT) pins (PA7 and PE0) with V_{DD} < 2 V	0.70 x V_{DD}	-	5.2	
		Input voltage on five-volt tolerant (FT) pins (PA7 and PE0) with $V_{DD} \geq 2$ V		-	5.5	
		Input voltage on 3.6 V tolerant (TT) pins		-	3.6	
		Input voltage on any other pin	0.70 x V_{DD}	-	V_{DD}+0.3	
V_{hys}	Schmitt trigger voltage hysteresis (3)	I/Os	-	200	-	mV
		True open drain I/Os	-	200	-	
I_{lkg}	Input leakage current (4)	$V_{SS} \leq V_{IN} \leq V_{DD}$ High sink I/Os	-	-	50 (5)	nA
		$V_{SS} \leq V_{IN} \leq V_{DD}$ True open drain I/Os	-	-	200(5)	
		$V_{SS} \leq V_{IN} \leq V_{DD}$ PA0 with high sink LED driver capability	-	-	200(5)	
R_{PU}	Weak pull-up equivalent resistor(2)(6)	$V_{IN}=V_{SS}$	30	45	60	kΩ
C_{IO}	I/O pin capacitance	-	-	5	-	pF

1. V_{DD} = 3.0 V, T_A = -40 to 125 °C unless otherwise specified.
2. Data based on characterization results.
3. Hysteresis voltage between Schmitt trigger switching levels. Based on characterization results, not tested.
4. The max. value may be exceeded if negative current is injected on adjacent pins.
5. Not tested in production.

Output driving current

Subject to general operating conditions for V_{DD} and T_A unless otherwise specified.

Table 39. Output driving current (high sink ports)

I/O Type	Symbol	Parameter	Conditions	Min	Max	Unit
High sink	V_{OL} (1)	Output low level voltage for an I/O pin	I_{IO} = +2 mA, V_{DD} = 3.0 V	-	0.45	V
			I_{IO} = +2 mA, V_{DD} = 1.8 V	-	0.45	V
			I_{IO} = +10 mA, V_{DD} = 3.0 V	-	0.7	V
	V_{OH} (2)	Output high level voltage for an I/O pin	I_{IO} = -2 mA, V_{DD} = 3.0 V	V_{DD}-0.45	-	V
			I_{IO} = -1 mA, V_{DD} = 1.8 V	V_{DD}-0.45	-	V
			I_{IO} = -10 mA, V_{DD} = 3.0 V	V_{DD}-0.7	-	V

1. The I_{IO} current sunk must always respect the absolute maximum rating specified in *Table 16* and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VSS}.
2. The I_{IO} current sourced must always respect the absolute maximum rating specified in *Table 16* and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VDD}.

Table 40. Output driving current (true open drain ports)

I/O Type	Symbol	Parameter	Conditions	Min	Max	Unit
Open drain	V_{OL} (1)	Output low level voltage for an I/O pin	I_{IO} = +3 mA, V_{DD} = 3.0 V	-	0.45	V
			I_{IO} = +1 mA, V_{DD} = 1.8 V	-	0.45	

1. The I_{IO} current sunk must always respect the absolute maximum rating specified in *Table 16* and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VSS}.

Table 41. Output driving current (PA0 with high sink LED driver capability)

I/O Type	Symbol	Parameter	Conditions	Min	Max	Unit
IR	V_{OL} (1)	Output low level voltage for an I/O pin	I_{IO} = +20 mA, V_{DD} = 2.0 V	-	0.45	V

1. The I_{IO} current sunk must always respect the absolute maximum rating specified in *Table 16* and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VSS}.

NRST pin

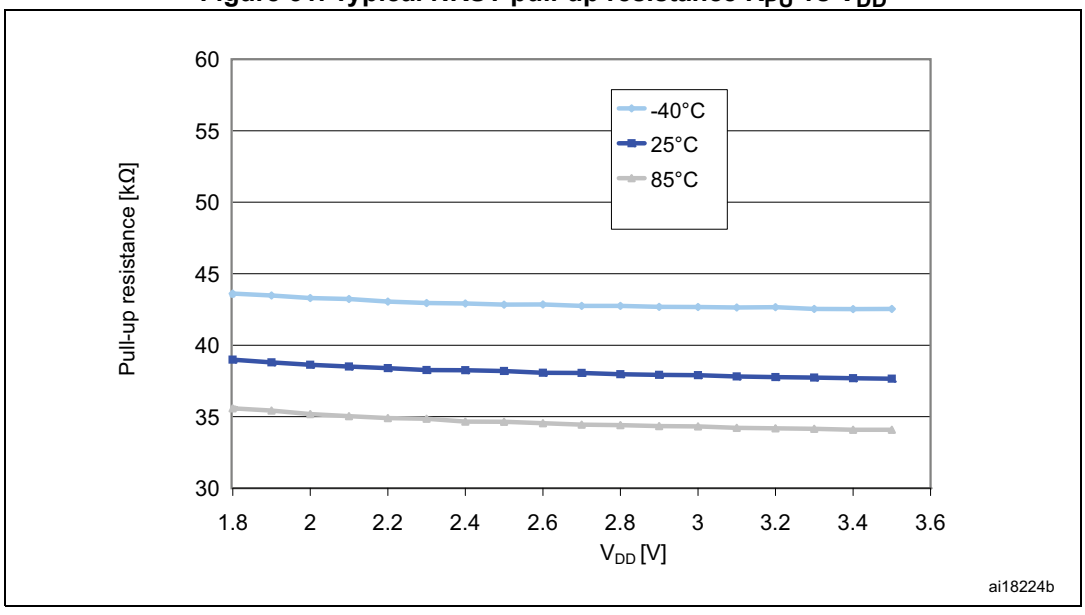
Subject to general operating conditions for V_{DD} and T_A unless otherwise specified.

Table 42. $\overline{\text{NRST}}$ pin characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{IL(NRST)}$	NRST input low level voltage (1)	-	V_{SS}	-	0.8	V
$V_{IH(NRST)}$	NRST input high level voltage (1)	-	1.4	-	V_{DD}	
$V_{OL(NRST)}$	NRST output low level voltage (1)	I_{OL} = 2 mA for 2.7 V ≤V_{DD} ≤3.6 V	-	-	0.4	
		I_{OL} = 1.5 mA for V_{DD} < 2.7 V	-	-		
V_{HYST}	NRST input hysteresis(3)	-	10%V_{DD} (2)	-	-	mV
$R_{PU(NRST)}$	NRST pull-up equivalent resistor (1)	-	30	45	60	kΩ
$V_{F(NRST)}$	NRST input filtered pulse (3)	-	-	-	50	ns
$V_{NF(NRST)}$	NRST input not filtered pulse (3)	-	300	-	-	

1. Data based on characterization results.
2. 200 mV min.
3. Data guaranteed by design.

Figure 31. Typical NRST pull-up resistance R_{PU} vs V_{DD}



9.3.11 Temperature sensor

In the following table, data is based on characterization results, not tested in production, unless otherwise specified.

Table 47. TS characteristics

Symbol	Parameter	Min	Typ	Max.	Unit
V_{90}(1)	Sensor reference voltage at 90°C ±5 °C,	0.580	0.597	0.614	V
T_L	V_{SENSOR} linearity with temperature	-	±1	±2	°C
Avg_slope (2)	Average slope	1.59	1.62	1.65	mV/°C
$I_{DD(TEMP)}$(2)	Consumption	-	3.4	6	µA
T_{START}(2)(3)	Temperature sensor startup time	-	-	10	µs
T_{S_TEMP}(2)	ADC sampling time when reading the temperature sensor	10	-	-	µs

1. Tested in production at V_{DD} = 3 V ±10 mV. The 8 LSB of the V_{90} ADC conversion result are stored in the TS_Factory_CONV_V90 byte.
2. Data guaranteed by design.
3. Defined for ADC output reaching its final value ±1/2LSB.

9.3.12 Comparator characteristics

In the following table, data is guaranteed by design, not tested in production, unless otherwise specified.

Table 48. Comparator 1 characteristics

Symbol	Parameter	Min	Typ	Max(1)	Unit
V_{DDA}	Analog supply voltage	1.65	-	3.6	V
T_A	Temperature range	-40	-	125	°C
R_{400K}	R_{400K} value	300	400	500	kΩ
R_{10K}	R_{10K} value	7.5	10	12.5	
V_{IN}	Comparator 1 input voltage range	0.6	-	V_{DDA}	V
V_{REFINT}	Internal reference voltage(2)	1.202	1.224	1.242	
t_{START}	Comparator startup time	-	7	10	µs
t_d	Propagation delay(3)	-	3	10	
V_{offset}	Comparator offset error	-	±3	±10	mV
I_{COMP1}	Current consumption(4)	-	160	260	nA

1. Based on characterization.
2. Tested in production at V_{DD} = 3 V ±10 mV.
3. The delay is characterized for 100 mV input step with 10 mV overdrive on the inverting input, the non-inverting input set to the reference.
4. Comparator consumption only. Internal reference voltage not included.

9.3.13 12-bit DAC characteristics

In the following table, data is guaranteed by design, not tested in production.

Table 50. DAC characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DDA}	Analog supply voltage	-	1.8	-	3.6	V
V_{REF+}	Reference supply voltage	-	1.8	-	V_{DDA}	
I_{VREF}	Current consumption on V_{REF+} supply	V_{REF+} = 3.3 V, no load, middle code (0x800)	-	130	220	µA
		V_{REF+} = 3.3 V, no load, worst code (0x000)	-	220	350	
I_{VDDA}	Current consumption on V_{DDA} supply	V_{DDA} = 3.3 V, no load, middle code (0x800)	-	210	320	
		V_{DDA} = 3.3 V, no load, worst code (0x000)	-	320	520	
T_A	Temperature range	-	-40	-	125	°C
R_L	Resistive load(1) (2)	DACOUT buffer ON	5	-	-	kΩ
R_O	Output impedance	DACOUT buffer OFF	-	8	10	kΩ
C_L	Capacitive load(3)	-	-	-	50	pF
DAC_OUT	DAC_OUT voltage(4)	DACOUT buffer ON	0.2	-	V_{DDA}-0.2	V
		DACOUT buffer OFF	0	-	V_{REF+} -1 LSB	V
$t_{settling}$	Settling time (full scale: for a 12-bit input code transition between the lowest and the highest input codes when DAC_OUT reaches the final value ±1LSB)	R_L ≥5 kΩ, C_L≤ 50 pF	-	7	12	µs
Update rate	Max frequency for a correct DAC_OUT (@95%) change when small variation of the input code (from code i to i+1LSB).	R_L ≥ 5 kΩ, C_L ≤50 pF	-		1	Msps
t_{WAKEUP}	Wakeup time from OFF state. Input code between lowest and highest possible codes.	R_L ≥5 kΩ, C_L≤50 pF	-	9	15	µs
PSRR+	Power supply rejection ratio (to V_{DDA}) (static DC measurement)	R_L≥ 5 kΩ, C_L≤50 pF	-	-60	-35	dB

1. Resistive load between DACOUT and GNDA.
2. Output on PF0 (48-pin package only).
3. Capacitive load at DACOUT pin.
4. It gives the output excursion of the DAC.

9.3.15 EMC characteristics

Susceptibility tests are performed on a sample basis during product characterization.

Functional EMS (electromagnetic susceptibility)

Based on a simple running application on the product (toggling 2 LEDs through I/O ports), the product is stressed by two electromagnetic events until a failure occurs (indicated by the LEDs).

- **ESD**: Electrostatic discharge (positive and negative) is applied on all pins of the device until a functional disturbance occurs. This test conforms with the IEC 61000 standard.
- **FTB**: A burst of fast transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test conforms with the IEC 61000 standard.

A device reset allows normal operations to be resumed. The test results are given in the table below based on the EMS levels and classes defined in application note AN1709.

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

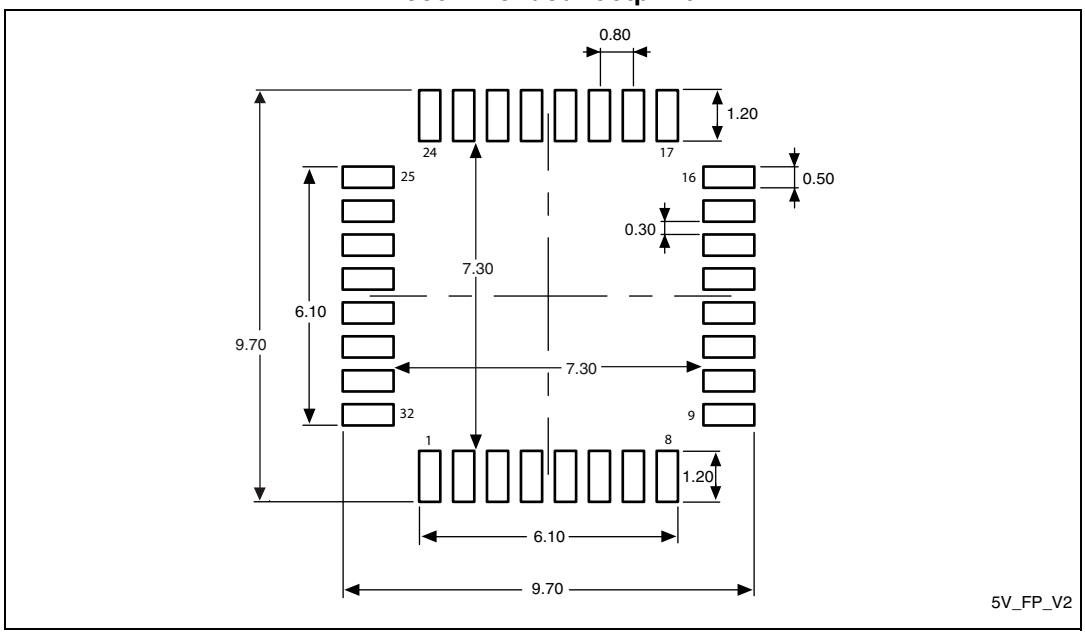
Table 58. EMS data

Symbol	Parameter	Conditions		Level/ Class
V_{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	V_{DD} = 3.3 V, T_A = +25 °C, f_{CPU}= 16 MHz, conforms to IEC 61000		3B
V_{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} pins to induce a functional disturbance	V_{DD} = 3.3 V, T_A = +25 °C, f_{CPU} = 16 MHz, conforms to IEC 61000	Using HSI	4A
			Using HSE	2B

Electromagnetic interference (EMI)

Based on a simple application running on the product (toggling 2 LEDs through the I/O ports), the product is monitored in terms of emission. This emission test is in line with the norm IEC61967-2 which specifies the board and the loading of each pin.

Figure 50. LQFP32 - 32-pin, 7 x 7 mm low-profile quad flat package recommended footprint

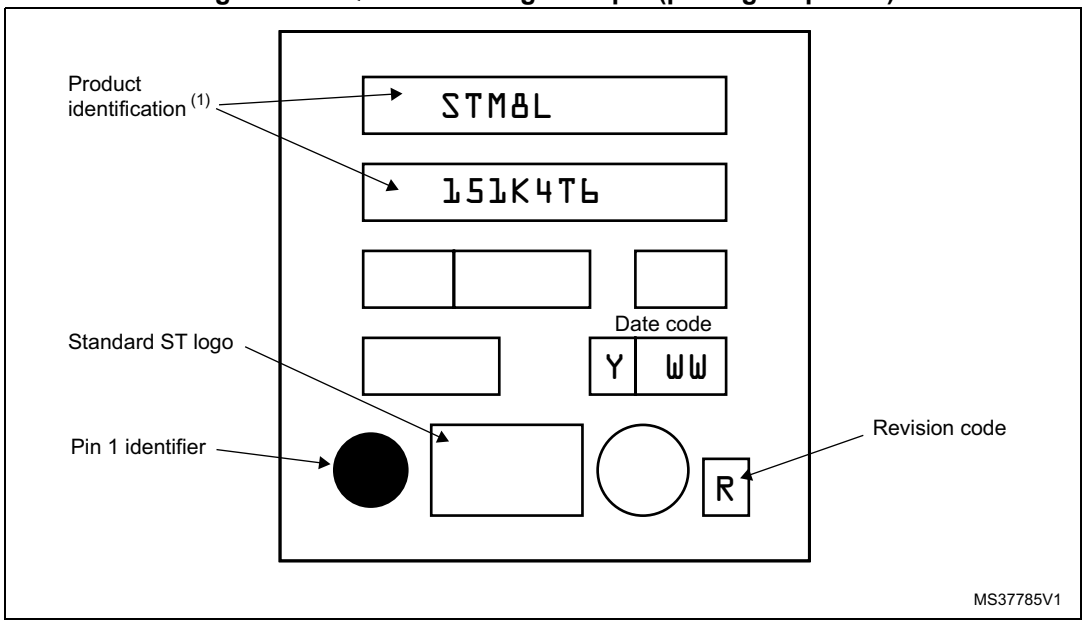


1. Dimensions are expressed in millimeters.

Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location. Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.

Figure 51. LQFP32 marking example (package top view)



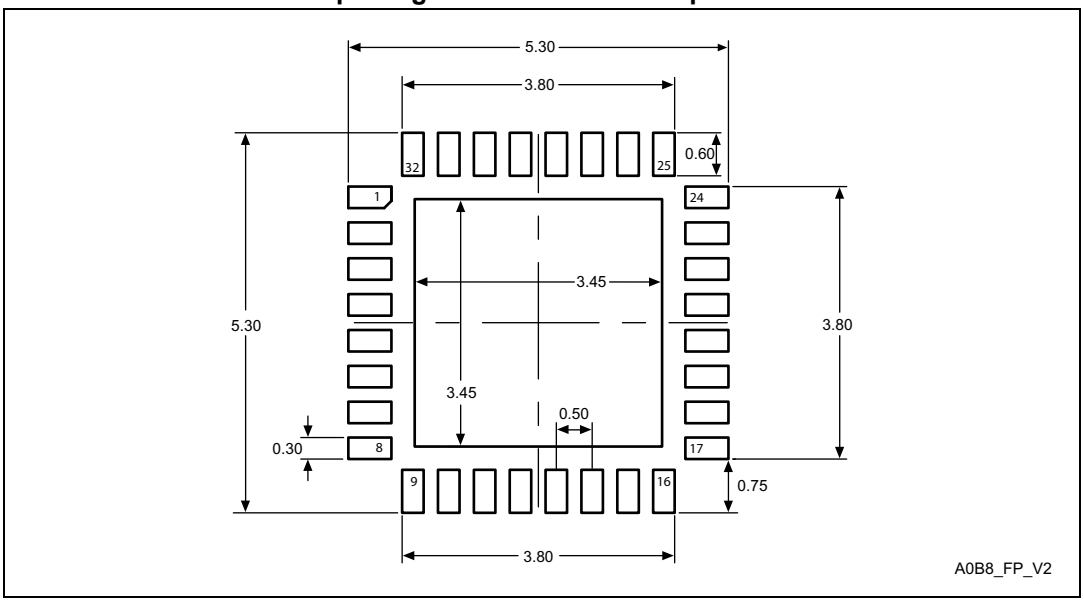
1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering

Table 65. UFQFPN32 - 32-pin, 5 x 5 mm, 0.5 mm pitch ultra thin fine pitch quad flat package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	0.500	0.550	0.600	0.0197	0.0217	0.0236
A1	0.000	0.020	0.050	0.0000	0.0008	0.0020
A3	-	0.152	-	-	0.0060	-
b	0.180	0.230	0.280	0.0071	0.0091	0.0110
D	4.900	5.000	5.100	0.1929	0.1969	0.2008
D1	3.400	3.500	3.600	0.1339	0.1378	0.1417
D2	3.400	3.500	3.600	0.1339	0.1378	0.1417
E	4.900	5.000	5.100	0.1929	0.1969	0.2008
E1	3.400	3.500	3.600	0.1339	0.1378	0.1417
E2	3.400	3.500	3.600	0.1339	0.1378	0.1417
e	-	0.500	-	-	0.0197	-
L	0.300	0.400	0.500	0.0118	0.0157	0.0197
ddd	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 53. UFQFPN32 - 32-pin, 5 x 5 mm, 0.5 mm pitch ultra thin fine pitch quad flat package recommended footprint

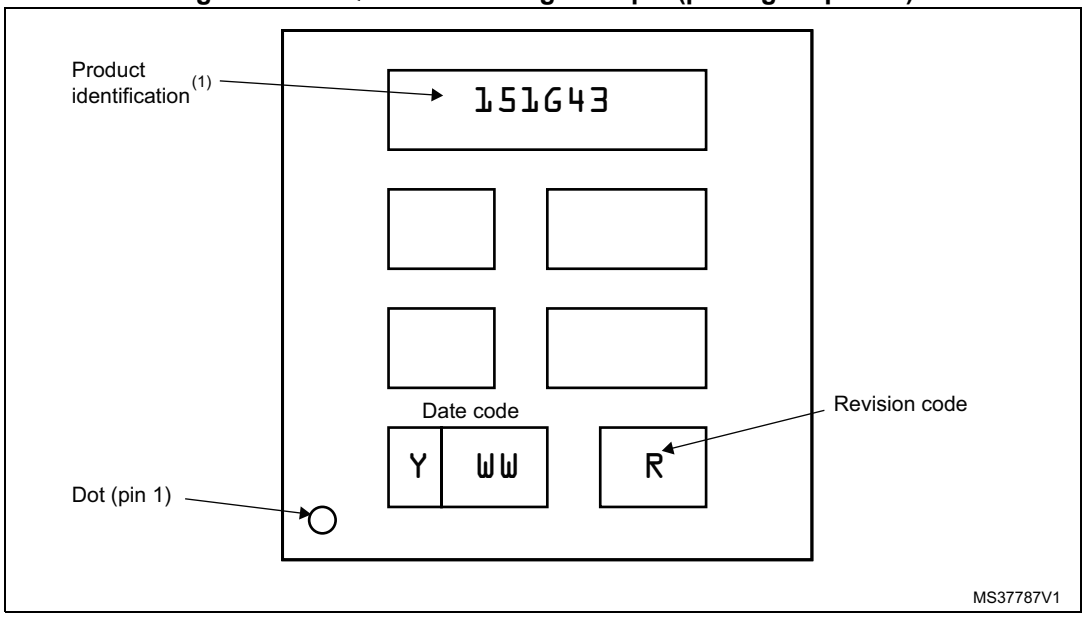


1. Dimensions are expressed in millimeters.

Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location. Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.

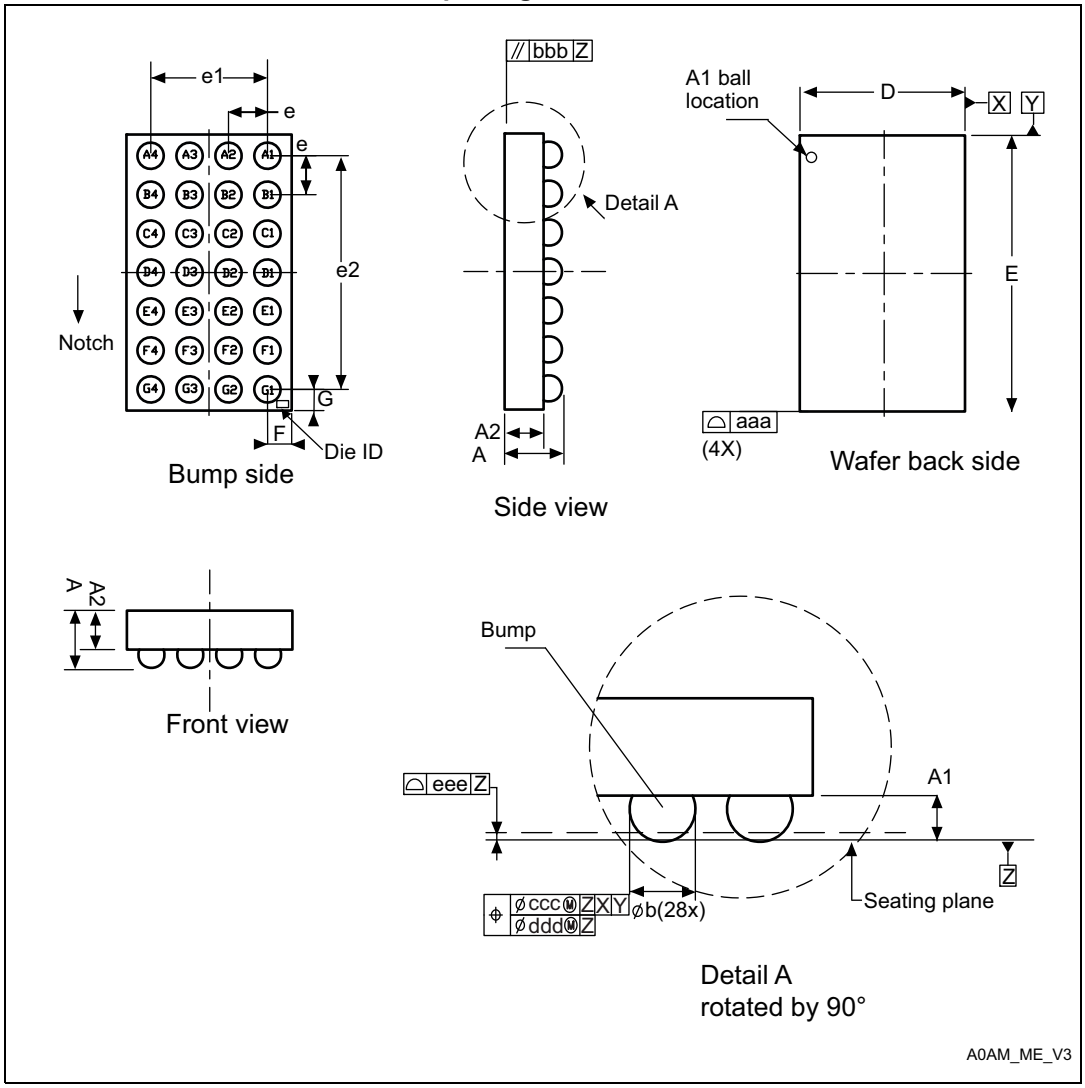
Figure 57. UFQFPN28 marking example (package top view)



1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.

10.7 WLCSP28 package information

Figure 58. WLCSP28 - 28-pin, 1.703 x 2.841 mm, 0.4 mm pitch wafer level chip scale package outline



1. Drawing is not to scale.

10.8 Thermal characteristics

The maximum chip junction temperature (T_{Jmax}) must never exceed the values given in *Table 18: General operating conditions on page 66*.

The maximum chip-junction temperature, T_{Jmax}, in degree Celsius, may be calculated using the following equation:

$$T_{Jmax} = T_{Amax} + (P_{Dmax} \times \Theta_{JA})$$

Where:

- T_{Amax} is the maximum ambient temperature in °C
- Θ_{JA} is the package junction-to-ambient thermal resistance in °C/W
- P_{Dmax} is the sum of P_{INTmax} and $P_{I/Omax}$ ($P_{Dmax} = P_{INTmax} + P_{I/Omax}$)
- P_{INTmax} is the product of I_{DD} and V_{DD}, expressed in Watts. This is the maximum chip internal power.
- $P_{I/Omax}$ represents the maximum power dissipation on output pins
  Where:
  $P_{I/Omax} = \Sigma (V_{OL}*I_{OL}) + \Sigma((V_{DD}-V_{OH})*I_{OH})$,
  taking into account the actual V_{OL}/I_{OL} and V_{OH}/I_{OH} of the I/Os at low and high level in the application.

Table 68. Thermal characteristics(1)

Symbol	Parameter	Value	Unit
Θ_{JA}	Thermal resistance junction-ambient LQFP 48- 7 x 7 mm	65	°C/W
Θ_{JA}	Thermal resistance junction-ambient UFQFPN 48- 7 x 7mm	32	°C/W
Θ_{JA}	Thermal resistance junction-ambient LQFP 32 - 7 x 7 mm	59	°C/W
Θ_{JA}	Thermal resistance junction-ambient UFQFPN 32 - 5 x 5 mm	38	°C/W
Θ_{JA}	Thermal resistance junction-ambient UFQFPN28 - 4 x 4 mm	118	°C/W
Θ_{JA}	Thermal resistance junction-ambient WLCSP28	70	°C/W

1. Thermal resistances are based on JEDEC JESD51-2 with 4-layer PCB in a natural convection environment.